Erratum to: Influence of Cd-rich Annealing on Defects in Te-rich CdZnTe Materials

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Following is the corrected caption of Fig. 6. The reference citation was missing in the original article.

Fig. 6. Evolution of the defect states of Te-rich materials during Cd-rich annealing. The T-X projection of the CdTe diagram in the figure is drawn based on Ref. 16.